



Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

FDP42AN15A0

N-Channel PowerTrench® MOSFET

150 V, 35 A, 42 mΩ

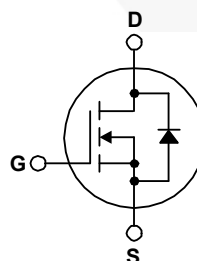
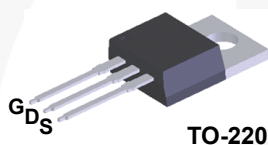
Features

- $R_{DS(on)} = 36 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 12 \text{ A}$
- $Q_{G(tot)} = 33 \text{ nC}$ (Typ.) @ $V_{GS} = 10 \text{ V}$
- Low Miller Charge
- Low Q_{rr} Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)

Applications

- Consumer Appliances
- Synchronous Rectification
- Uninterruptible Power Supply
- Micro Solar Inverter

Formerly developmental type 82864



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FDP42AN15A0	Unit
V_{DSS}	Drain to Source Voltage	150	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current		
	Continuous ($T_C = 25^\circ\text{C}$, $V_{GS} = 10\text{V}$)	35	A
	Continuous ($T_C = 100^\circ\text{C}$, $V_{GS} = 10\text{V}$)	24	
	Continuous ($T_{amb} = 25^\circ\text{C}$, $V_{GS} = 10\text{V}$, with $R_{\theta JA} = 43^\circ\text{C/W}$)	5	A
	Pulsed	Figure 4	A
E_{AS}	Single Pulse Avalanche Energy (Note 1)	90	mJ
P_D	Power dissipation	150	W
	Derate above 25°C	1.00	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.0	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP42AN15A0	FDP42AN15A0	TO-220	Tube	N/A	50 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
--------	-----------	-----------------	-----	-----	-----	------

Off Characteristics

$B_{V_{DS}}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	150	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 120\text{V}$ $V_{GS} = 0\text{V}$ $T_C = 150^\circ\text{C}$	-	-	1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(TH)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	2	-	4	V
$r_{DS(ON)}$	Drain to Source On Resistance	$I_D = 12\text{A}, V_{GS} = 10\text{V}$	-	0.036	0.042	Ω
		$I_D = 6\text{A}, V_{GS} = 6\text{V}$	-	0.040	0.060	
		$I_D = 12\text{A}, V_{GS} = 10\text{V},$ $T_J = 175^\circ\text{C}$	-	0.090	0.107	

Dynamic Characteristics

C_{ISS}	Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}$	-	2150	-	pF
C_{OSS}	Output Capacitance		-	225	-	pF
C_{RSS}	Reverse Transfer Capacitance		-	45	-	pF
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0\text{V to } 10\text{V}$	-	30	39	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0\text{V to } 2\text{V}$	-	4.2	5.4	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DD} = 75\text{V}$ $I_D = 12\text{A}$ $I_g = 1.0\text{mA}$	-	9.5	-	nC
Q_{gs2}	Gate Charge Threshold to Plateau		-	5.3	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	6.9	-	nC

Switching Characteristics ($V_{GS} = 10\text{V}$)

t_{ON}	Turn-On Time	$V_{DD} = 75\text{V}, I_D = 12\text{A}$ $V_{GS} = 10\text{V}, R_{GS} = 7.5\Omega$	-	-	46	ns
$t_{d(ON)}$	Turn-On Delay Time		-	11	-	ns
t_r	Rise Time		-	19	-	ns
$t_{d(OFF)}$	Turn-Off Delay Time		-	27	-	ns
t_f	Fall Time		-	23	-	ns
t_{OFF}	Turn-Off Time		-	-	74	ns

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 12\text{A}$	-	-	1.25	V
		$I_{SD} = 6\text{A}$	-	-	1.0	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 12\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	82	ns
Q_{RR}	Reverse Recovered Charge	$I_{SD} = 12\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	204	nC

Notes:

1: Starting $T_J = 25^\circ\text{C}$, $L = 0.2\text{mH}$, $I_{AS} = 30\text{A}$.

Typical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

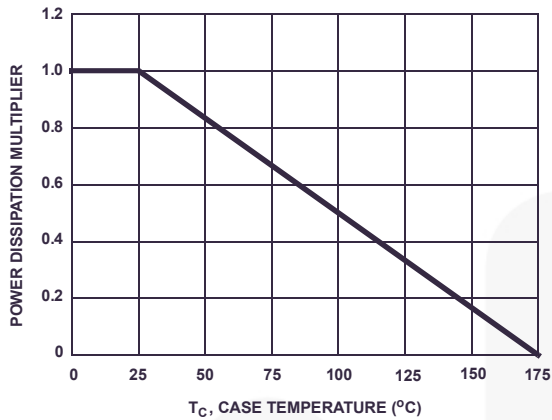


Figure 1. Normalized Power Dissipation vs Ambient Temperature

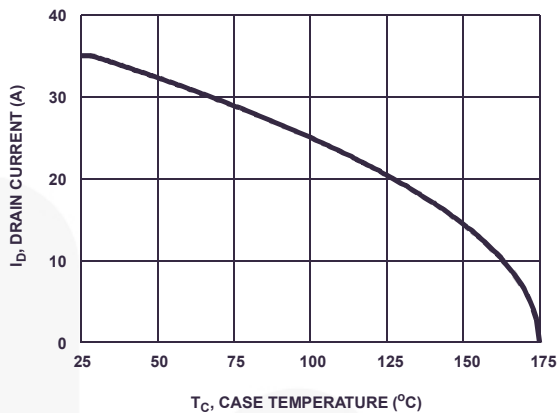


Figure 2. Maximum Continuous Drain Current vs Case Temperature

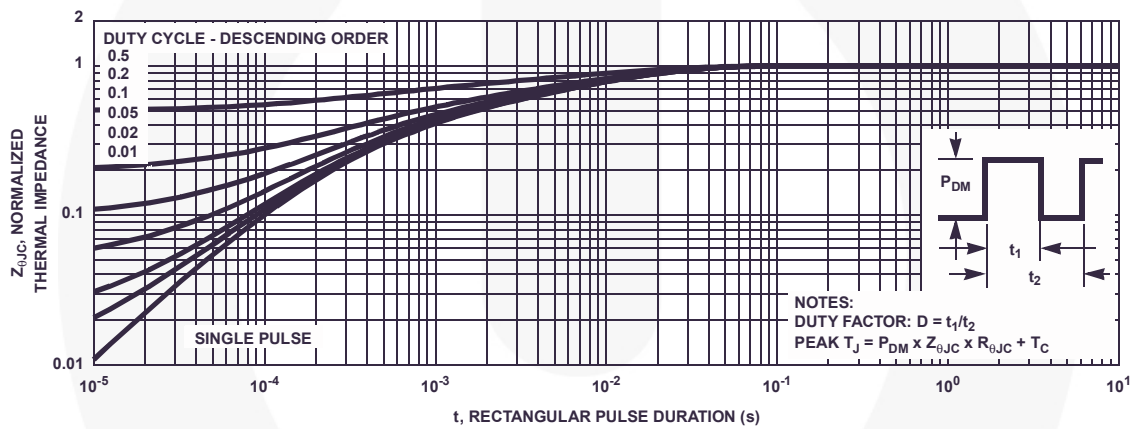


Figure 3. Normalized Maximum Transient Thermal Impedance

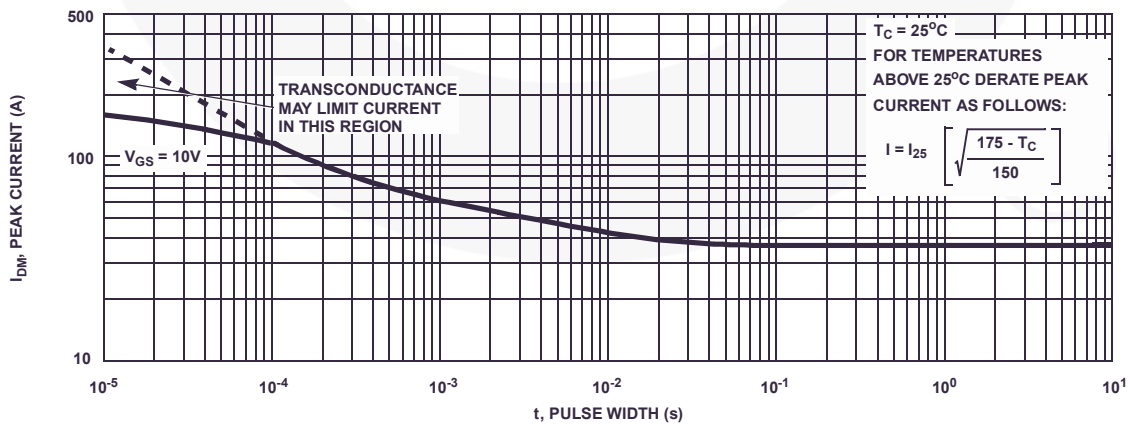


Figure 4. Peak Current Capability

Typical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

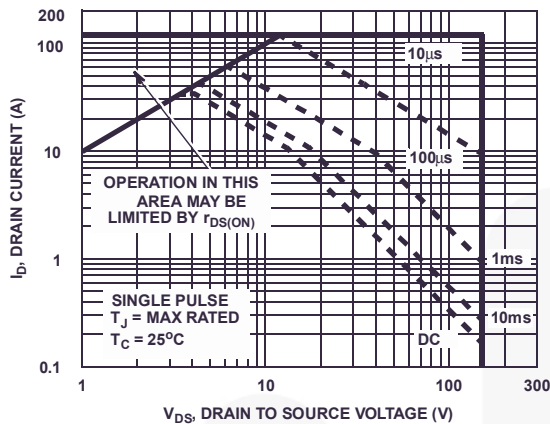
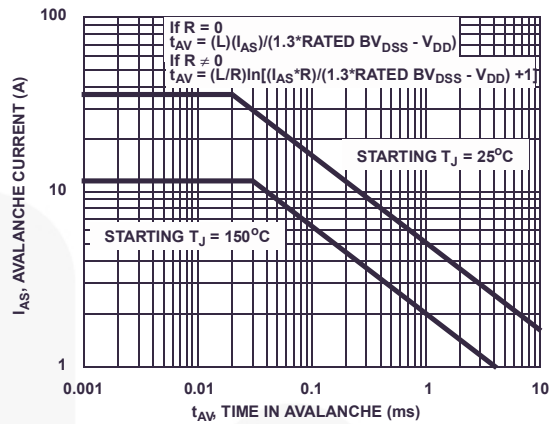


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

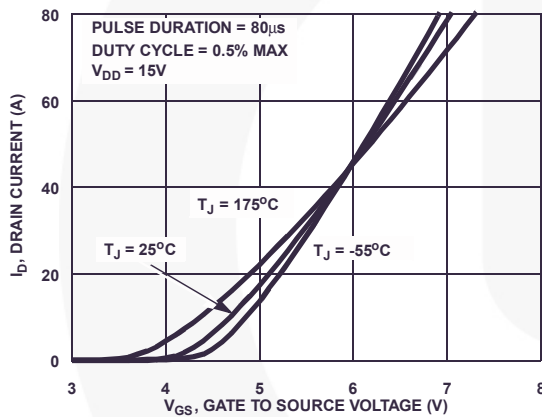


Figure 7. Transfer Characteristics

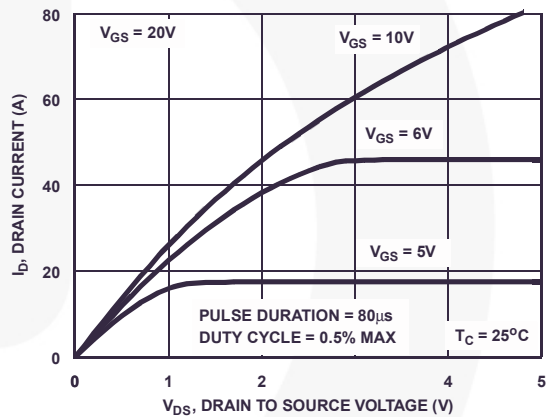


Figure 8. Saturation Characteristics

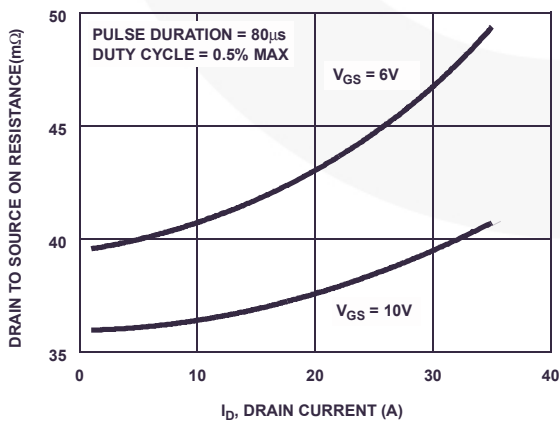


Figure 9. Drain to Source On Resistance vs Drain Current

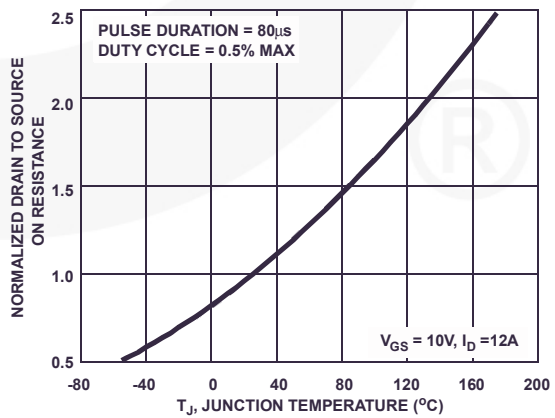


Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

Typical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

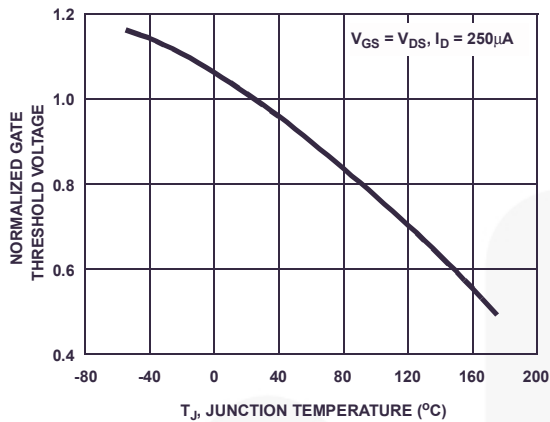


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

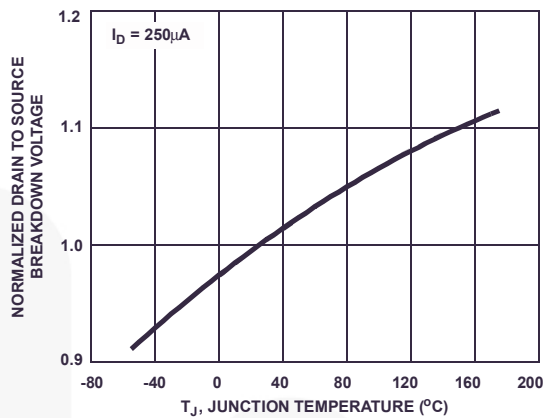


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

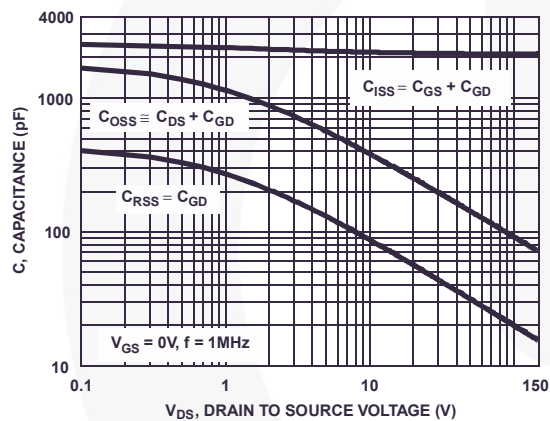


Figure 13. Capacitance vs Drain to Source Voltage

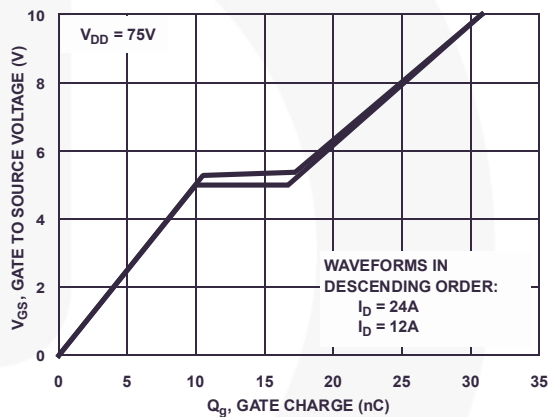


Figure 14. Gate Charge Waveforms for Constant Gate Current

Test Circuits and Waveforms

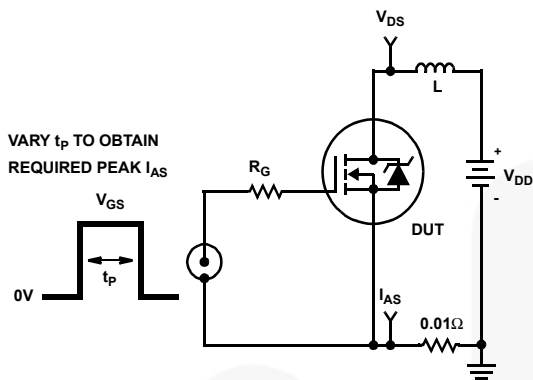


Figure 15. Unclamped Energy Test Circuit



Figure 16. Unclamped Energy Waveforms

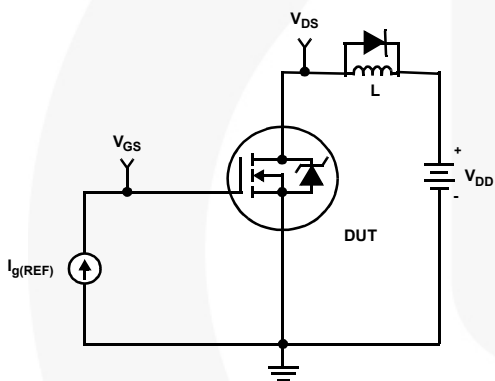


Figure 17. Gate Charge Test Circuit



Figure 18. Gate Charge Waveforms



Figure 19. Switching Time Test Circuit



Figure 20. Switching Time Waveforms

PSPICE Electrical Model

.SUBCKT FDB42AN15A0 2 1 3 ; rev June 11, 2002
 Ca 12 8 6.0e-10
 Cb 15 14 8e-10
 Cin 6 8 2.1e-9

Dbody 7 5 DbodyMOD
 Dbreak 5 11 DbreakMOD
 Dplcap 10 5 DplcapMOD

Ebbreak 11 7 17 18 159.5
 Eds 14 8 5 8 1
 Egs 13 8 6 8 1
 Esg 6 10 6 8 1
 Evthres 6 21 19 8 1
 Evtemp 20 6 18 22 1

It 8 17 1

Lgate 1 9 4.81e-9
 Ldrain 2 5 1.0e-9
 Lsource 3 7 4.63e-9

RLgate 1 9 48.1
 RLdrain 2 5 10
 RLsource 3 7 46.3

Mmed 16 6 8 8 MmedMOD
 Mstro 16 6 8 8 MstroMOD
 Mweak 16 21 8 8 MweakMOD

Rbreak 17 18 RbreakMOD 1
 Rdrain 50 16 RdrainMOD 14e-3
 Rgate 9 20 1.36
 RSLC1 5 51 RSLCMOD 1e-6
 RSLC2 5 50 1e3
 Rsource 8 7 RsourceMOD 20e-3
 Rvthres 22 8 RvthresMOD 1
 Rvtemp 18 19 RvtempMOD 1
 S1a 6 12 13 8 S1AMOD
 S1b 13 12 13 8 S1BMOD
 S2a 6 15 14 13 S2AMOD
 S2b 13 15 14 13 S2BMOD

Vbat 22 19 DC 1

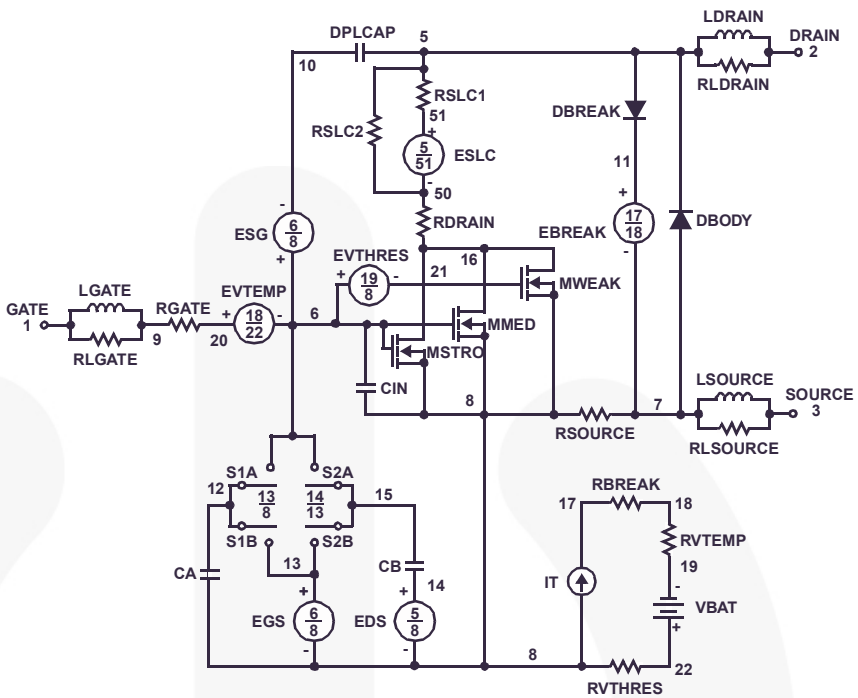
ESLC 51 50 VALUE={(V(5,51)/ABS(V(5,51)))*(PWR(V(5,51))/(1e-6*65),3))}

.MODEL DbodyMOD D (IS=2.4E-11 N=1.08 RS=4.2e-3 TRS1=2.2e-3 TRS2=2.5e-9
 + CJO=1.35e-9 M=6.3e-1 TT=4.8e-8 XTI=3.9)
 .MODEL DbreakMOD D (RS=1.5e-1 TRS1=1e-3 TRS2=-8.9e-6)
 .MODEL DplcapMOD D (CJO=.43e-9 IS=1e-30 N=10 M=0.66)
 .MODEL MmedMOD NMOS (VTO=3.5 KP=4 IS=1e-30 N=10 TOX=1 L=1u W=1u RG=9.3e-1)
 .MODEL MstroMOD NMOS (VTO=4.0 KP=70 IS=1e-30 N=10 TOX=1 L=1u W=1u)
 .MODEL MweakMOD NMOS (VTO=3.12 KP=0.06 IS=1e-30 N=10 TOX=1 L=1u W=1u RG=9.3e-1 RS=.1)

.MODEL RbreakMOD RES (TC1=1e-3 TC2=-15e-7)
 .MODEL RdrainMOD RES (TC1=1.7e-2 TC2=4e-5)
 .MODEL RSLCMOD RES (TC1=2.5e-3 TC2=1e-6)
 .MODEL RsourceMOD RES (TC1=1e-3 TC2=1e-6)
 .MODEL RvthresMOD RES (TC1=-5.3e-3 TC2=-1.5e-5)
 .MODEL RvtempMOD RES (TC1=-2.7e-3 TC2=1e-6)

.MODEL S1AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-4 VOFF=-1.5)
 .MODEL S1BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-1.5 VOFF=-4)
 .MODEL S2AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-1 VOFF=0.5)
 .MODEL S2BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=0.5 VOFF=-1)
 .ENDS

Note: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.



SABER Electrical Model

rev June 11, 2002
 template FDB42AN15A0 n2,n1,n3
 electrical n2,n1,n3

```
{
var i iscl
dp..model dbodymod = (isl=2.4e-11,nl=1.08,rs=4.2e-3,trs1=2.2e-3,trs2=2.5e-9,cjo=1.35e-9,m=6.3e-1,tt=4.8e-8,xti=3.9)
dp..model dbreakmod = (rs=1.5e-1,trs1=1e-3,trs2=-8.9e-6)
dp..model dplcapmod = (cjo=.43e-9,isl=10e-30,nl=10,m=0.66)
m..model mmedmod = (type=_n,vto=3.5,kp=4,is=1e-30,tox=1)
m..model mstrongmod = (type=_n,vto=4.0,kp=70,is=1e-30,tox=1)
m..model mweakmod = (type=_n,vto=3.12,kp=0.06,is=1e-30,tox=1,rs=1)
sw_vcsp..model s1amod = (ron=1e-5,roff=0.1,von=-4,voff=-1.5)
sw_vcsp..model s1bmod = (ron=1e-5,roff=0.1,von=-1.5,voff=-4)
sw_vcsp..model s2amod = (ron=1e-5,roff=0.1,von=-1,voff=0.5)
sw_vcsp..model s2bmod = (ron=1e-5,roff=0.1,von=0.5,voff=-1)
c.ca n12 n8 = 6.0e-10
c.cb n15 n14 = 8e-10
c.cin n6 n8 = 2.1e-9
```

```
dp.dbody n7 n5 = model=dbodymod
dp.dbreak n5 n11 = model=dbreakmod
dp.dplcap n10 n5 = model=dplcapmod
```

```
spe.ebreak n11 n7 n17 n18 = 159.5
spe.eds n14 n8 n5 n8 = 1
spe.egs n13 n8 n6 n8 = 1
spe.esg n6 n10 n6 n8 = 1
spe.evthres n6 n21 n19 n8 = 1
spe.evtemp n20 n6 n18 n22 = 1
```

```
i.it n8 n17 = 1
```

```
l.lgate n1 n9 = 4.81e-9
l.ldrain n2 n5 = 1.0e-9
l.lsource n3 n7 = 4.63e-9
```

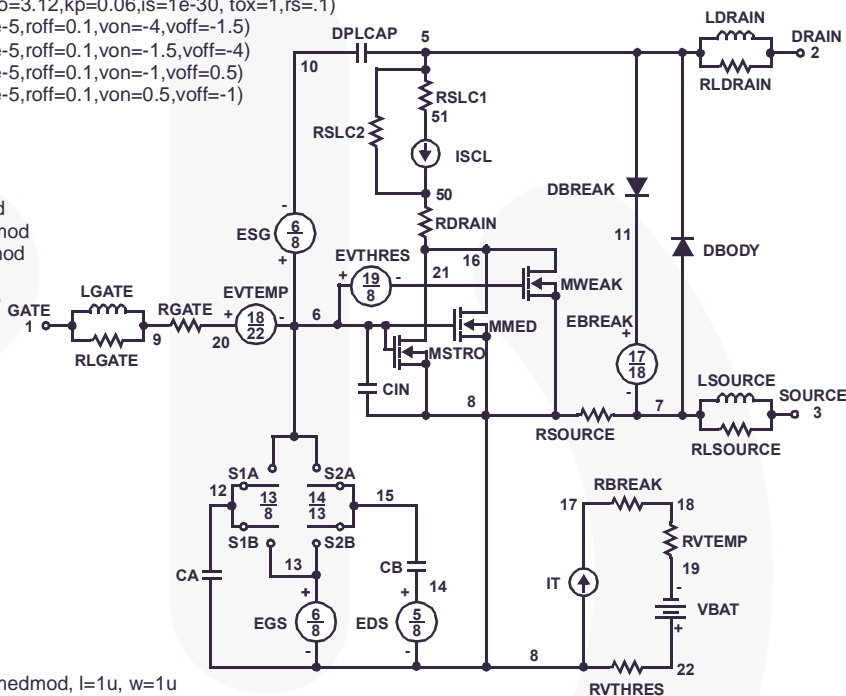
```
res.rlgate n1 n9 = 48.1
res.rldrain n2 n5 = 10
res.rlsource n3 n7 = 46.3
```

```
m.mmed n16 n6 n8 n8 = model=mmedmod, l=1u, w=1u
m.mstrong n16 n6 n8 n8 = model=mstrongmod, l=1u, w=1u
m.mweak n16 n21 n8 n8 = model=mweakmod, l=1u, w=1u
```

```
res.rbreak n17 n18 = 1, tc1=1e-3,tc2=-15e-7
res.rdrain n50 n16 = 14e-3, tc1=1.7e-2,tc2=4e-5
res.rgate n9 n20 = 1.36
res.rslc1 n5 n51 = 1e-6, tc1=2.5e-3,tc2=1e-6
res.rslc2 n5 n50 = 1e3
res.rsource n8 n7 = 20e-3, tc1=1e-3,tc2=1e-6
res.rvthres n22 n8 = 1, tc1=-5.3e-3,tc2=-1.5e-5
res.rvtemp n18 n19 = 1, tc1=-2.7e-3,tc2=1e-6
sw_vcsp.s1a n6 n12 n13 n8 = model=s1amod
sw_vcsp.s1b n13 n12 n13 n8 = model=s1bmod
sw_vcsp.s2a n6 n15 n14 n13 = model=s2amod
sw_vcsp.s2b n13 n15 n14 n13 = model=s2bmod
```

```
v.vbat n22 n19 = dc=1
```

```
equations {
i (n51->n50) +=iscl
iscl: v(n51,n50) = (((v(n5,n51))/(1e-9+abs(v(n5,n51))))*((abs(v(n5,n51))*1e6/65)** 3)))
}
```



SPICE Thermal Model

REV 23 June 11, 2002

FDB42AN15A0_Thermal

```

CTHERM1 TH 6 2e-3
CTHERM2 6 5 4.5e-3
CTHERM3 5 4 7e-3
CTHERM4 4 3 3e-2
CTHERM5 3 2 4e-2
CTHERM6 2 TL 8.5e-1
    
```

```

R THERM1 TH 6 6.2e-2
R THERM2 6 5 8.2e-2
R THERM3 5 4 9.2e-2
R THERM4 4 3 9.7e-2
R THERM5 3 2 0.2
R THERM6 2 TL 0.22
    
```

SABER Thermal Model

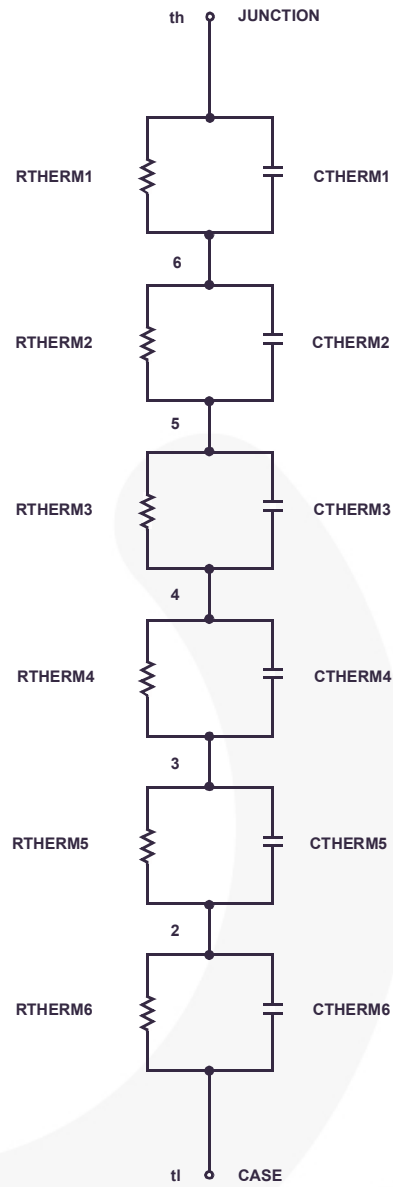
SABER thermal model FDB42AN15A0_Thermal
 template thermal_model th tl
 thermal_c th, tl

```

{
ctherm.ctherm1 th 6 =2e-3
ctherm.ctherm2 6 5 =4.5e-3
ctherm.ctherm3 5 4 =7e-3
ctherm.ctherm4 4 3 =3e-2
ctherm.ctherm5 3 2 =4e-2
ctherm.ctherm6 2 tl =8.5e-1
    
```

```

rtherm.rtherm1 th 6 =6.2e-2
rtherm.rtherm2 6 5 =8.2e-2
rtherm.rtherm3 5 4 =9.2e-2
rtherm.rtherm4 4 3 =9.7e-2
rtherm.rtherm5 3 2 =0.2
rtherm.rtherm6 2 tl =0.22}
    
```



Mechanical Dimensions

TO-220 3L

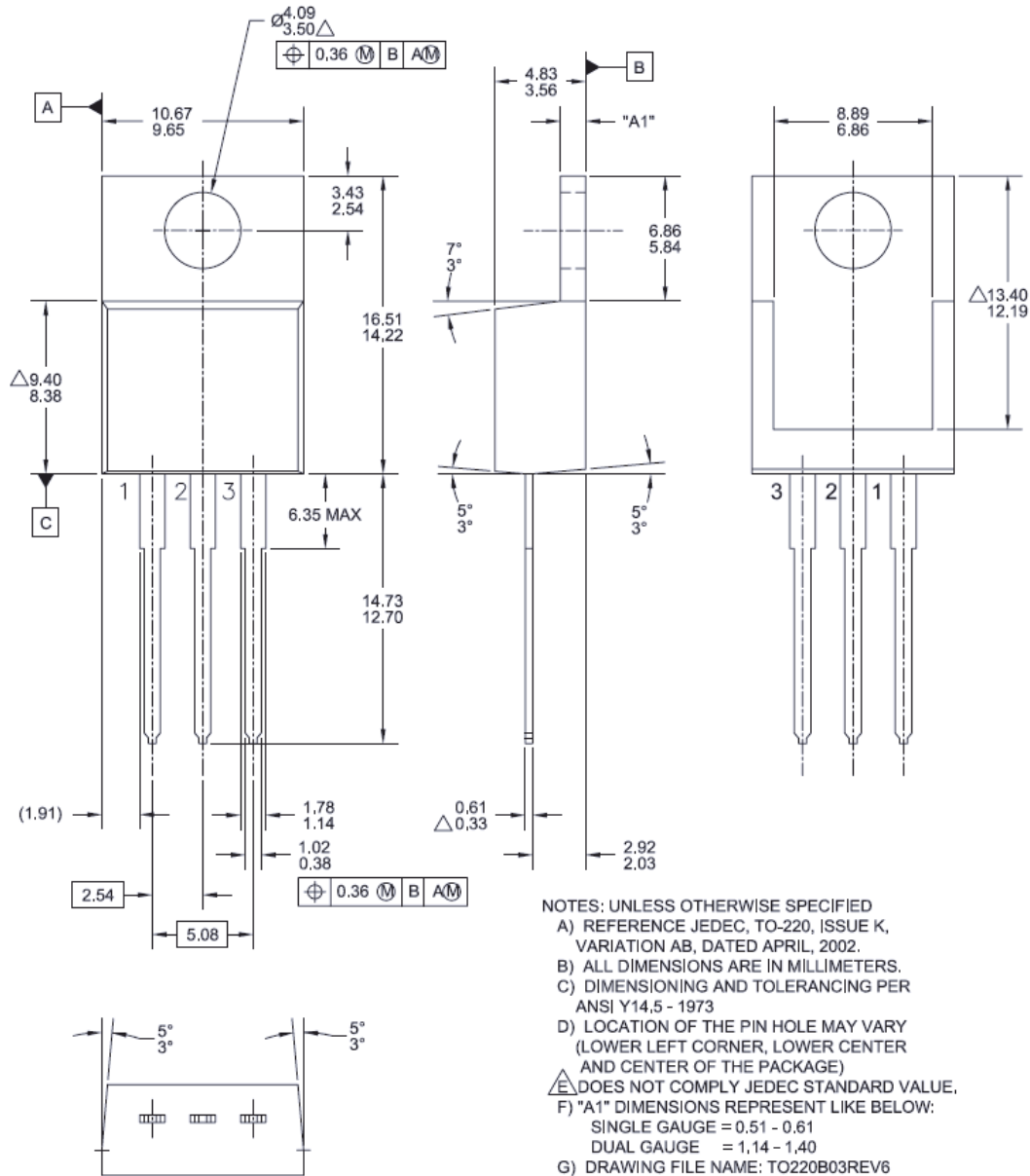


Figure 21. TO-220, Molded, 3Lead, Jedec Variation AB

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT220-003

Dimension in Millimeters

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>
For additional information, please contact your local
Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[ON Semiconductor:](#)

[FDP42AN15A0_Q](#) [FDP42AN15A0](#)



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.